

Load Switch with Level-Shift

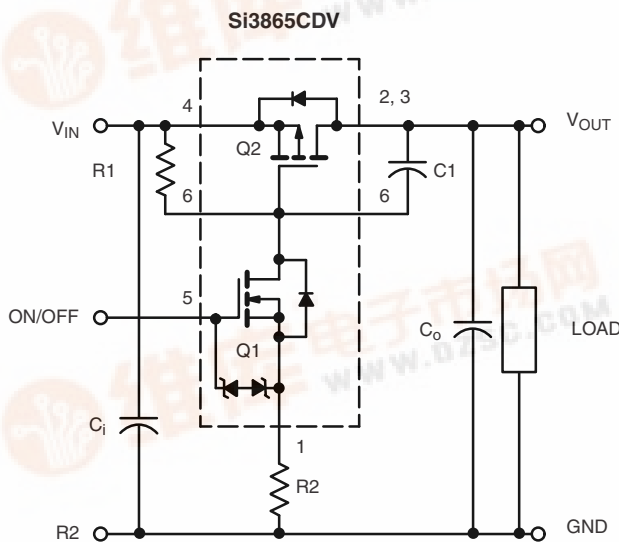
PRODUCT SUMMARY

V_{DS2} (V) (V_{IN})	$R_{DS(on)}$ (Ω)	I_D (A)
1.8 to 12	0.060 at $V_{IN} = 4.5$ V	2.8
	0.095 at $V_{IN} = 2.5$ V	2.2
	0.130 at $V_{IN} = 1.8$ V	1.9

DESCRIPTION

The Si3865CDV includes a P- and N-Channel MOSFET in a single TSOP-6 package. The low on-resistance P-Channel TrenchFET is tailored for use as a load switch. The N-Channel, with an external resistor, can be used as a level-

APPLICATION CIRCUITS



COMPONENTS

R1	Pull-Up Resistor	Typical 10 k Ω to 1 M Ω *
R2	Optional Slew-Rate Control	Typical 0 to 100 k Ω *
C1	Optional Slew-Rate Control	Typical 1000 pF

Note:

* Minimum R1 value should be at least 10 x R2 to ensure Q1 turn-on at 1.8 V input.

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- 60 m Ω Low $R_{DS(on)}$ TrenchFET[®]
- 1.8 V to 12 V Input
- 1.5 V to 8 V Logic Level Control
- Low Profile, Small Footprint TSOP-6 Package
- 3000 V ESD Protection On Input Switch, $V_{ON/OFF}$
- Adjustable Slew-Rate
- Compliant to RoHS Directive 2002/95/EC

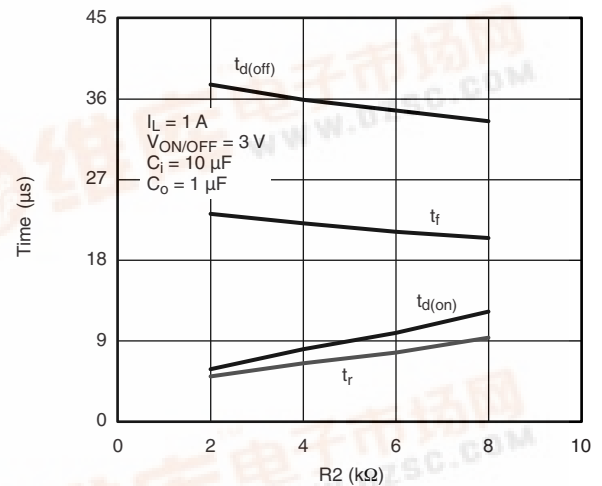


RoHS
COMPLIANT
HALOGEN
FREE
Available

APPLICATIONS

- Load Switching for Portable Devices

shift to drive the P-Channel load-switch. The N-Channel MOSFET has internal ESD protection and can be driven by logic signals as low as 1.5 V. The Si3865CDV operates on supply lines from 1.8 to 12 V, and can drive loads up to 2.8 A.



Switching Variation
R2 at $V_{IN} = 2.5$ V, $R1 = 20$ k Ω

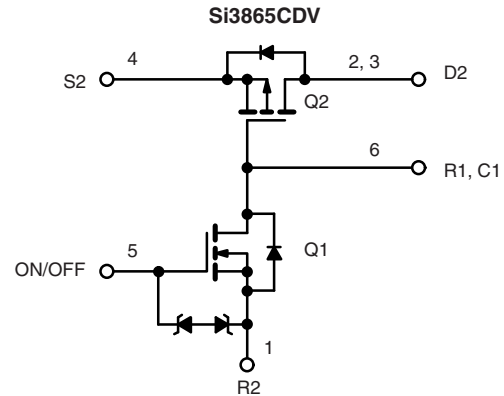
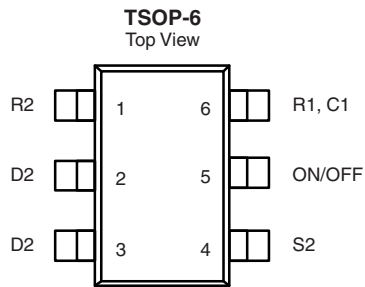
The Si3865CDV is ideally suited for high-side load switching in portable applications. The integrated N-Channel level-shift device saves space by reducing external components. The slew rate is set externally so that rise-times can be tailored to different load types.

Si3865CDV

Vishay Siliconix 供应商



FUNCTIONAL BLOCK DIAGRAM



Ordering Information: Si3865CDV-T1-E3 (Lead (Pb)-free)
Si3865CDV-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

Parameter	Symbol	Limit	Unit
Input Voltage	V_{IN} (V_{DS2})	12	V
Gate-Source Voltage	V_{GS2}	8	
ON/OFF Voltage	$V_{ON/OFF}$ (V_{GS1})	8	
Load Current	Continuous ^{a, b}	± 2.8	A
	Pulsed ^{b, c}	± 6	
Continuous Intrinsic Diode Conduction ^a	I_S	- 1	
Maximum Power Dissipation ^a	P_D	0.83	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150	$^{\circ}\text{C}$
ESD Rating, MIL-STD-883D Human Body Model (100 pF, 1500 Ω)	ESD	3	kV

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient (continuous current) ^a	R_{thJA}	130	150	$^{\circ}\text{C}/\text{W}$
Maximum Junction-to-Foot (Q2)	R_{thJF}	75	90	

SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)

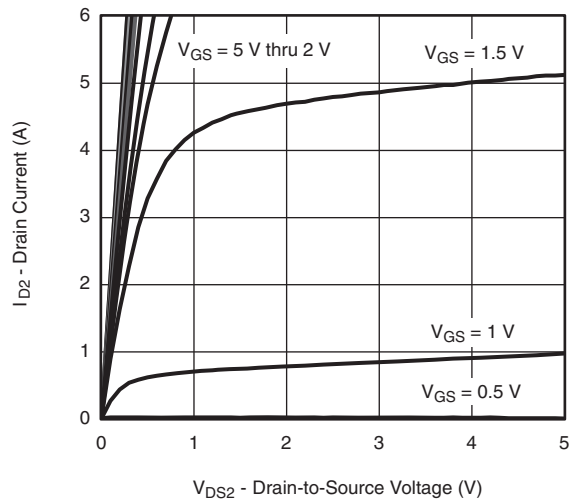
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF Characteristics						
Reverse Leakage Current	I_{FL}	$V_{IN} = 12\text{ V}, V_{ON/OFF} = 0\text{ V}$			1	μA
Diode Forward Voltage	V_{SD}	$I_S = -1\text{ A}$		- 0.77	- 1	V
ON Characteristics						
Input Voltage Range	V_{IN} (V_{DS2})		1.8		12	V
On-Resistance (P-Channel) at 1 A	$R_{DS(on)}$	$V_{ON/OFF} = 1.5\text{ V}, I_D = 1\text{ A}$	$V_{IN} = 4.5\text{ V}$	0.050	0.060	Ω
			$V_{IN} = 2.5\text{ V}$	0.073	0.095	
			$V_{IN} = 1.8\text{ V}$	0.100	0.130	
On-State (P-Channel) Drain-Current	$I_{D(on)}$	$V_{IN-OUT} \leq 0.2\text{ V}, V_{IN} = 5\text{ V}, V_{ON/OFF} = 1.5\text{ V}$	1			A
		$V_{IN-OUT} \leq 0.3\text{ V}, V_{IN} = 3\text{ V}, V_{ON/OFF} = 1.5\text{ V}$	1			

Notes:

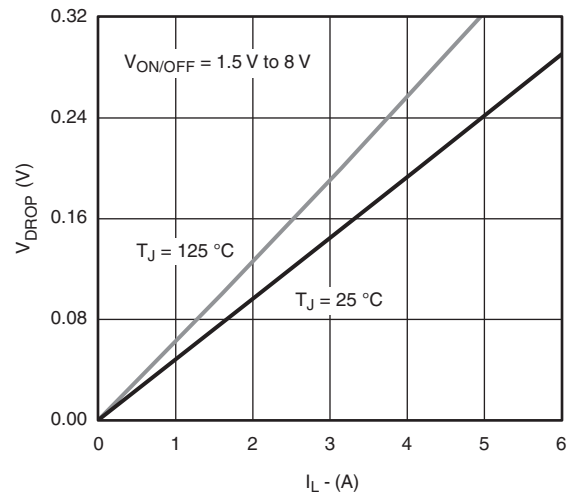
- a. Surface Mounted on FR4 board.
b. $V_{IN} = 8\text{ V}, V_{ON/OFF} = 8\text{ V}, T_A = 25\text{ }^{\circ}\text{C}$.
c. Pulse test: pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

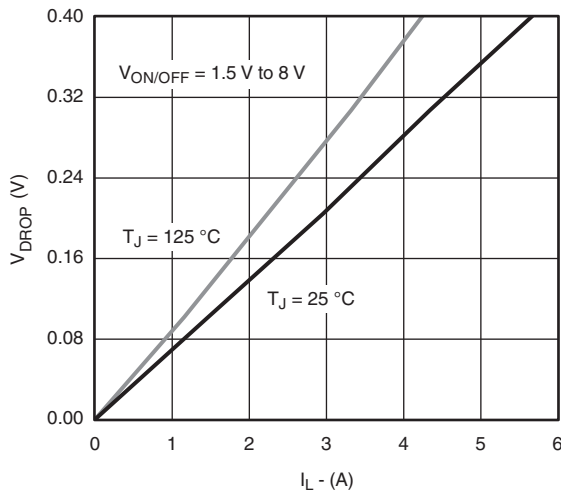
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



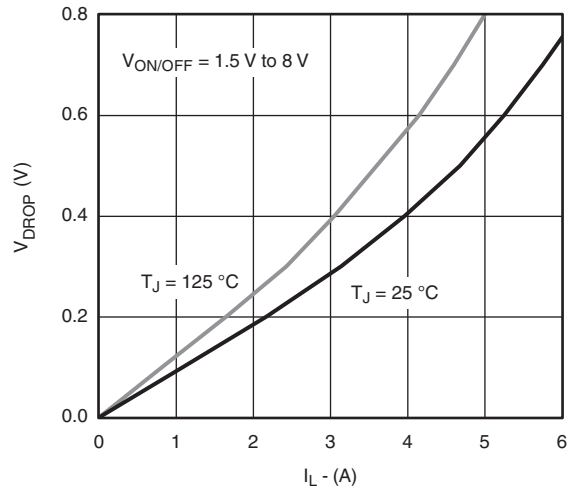
Output Characteristics



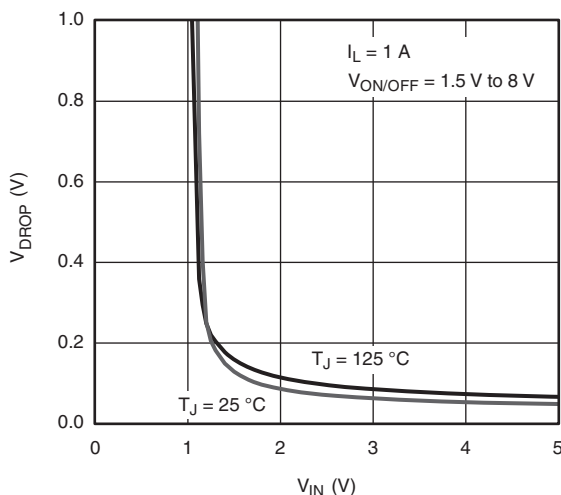
V_{DROP} vs. I_L at $V_{IN} = 4.5\text{ V}$



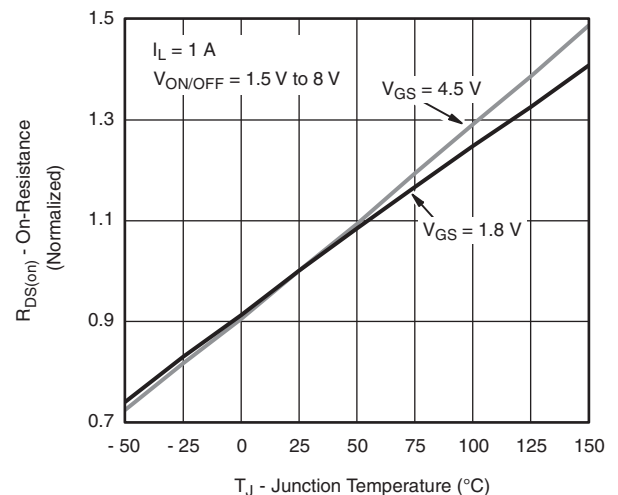
V_{DROP} vs. I_L at $V_{IN} = 2.5\text{ V}$



V_{DROP} vs. I_L at $V_{IN} = 1.8\text{ V}$



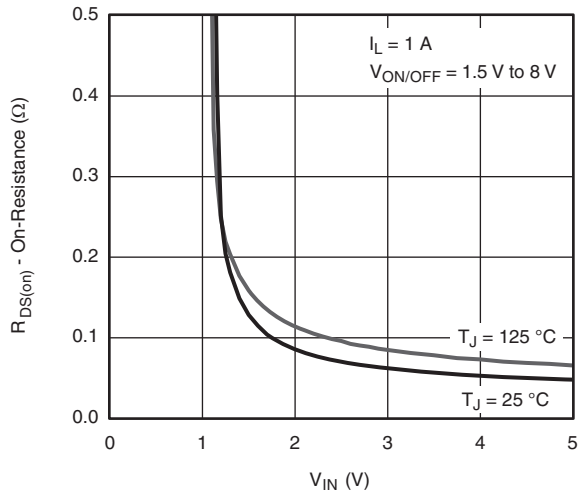
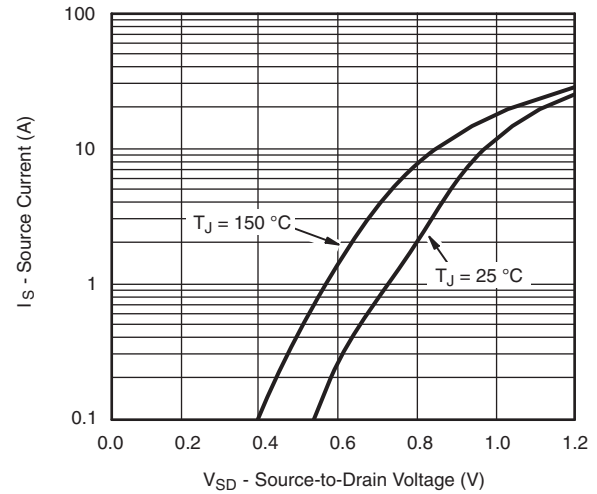
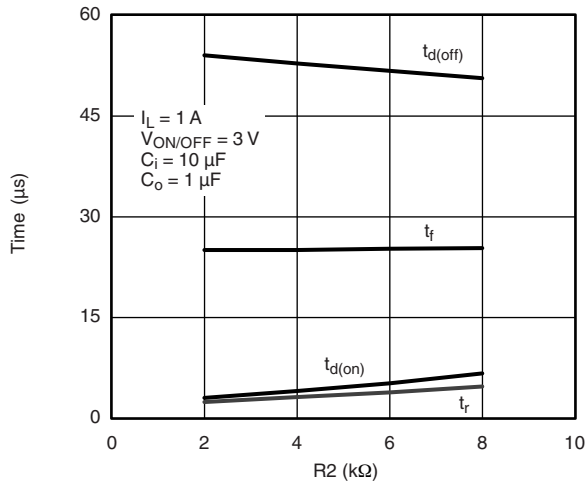
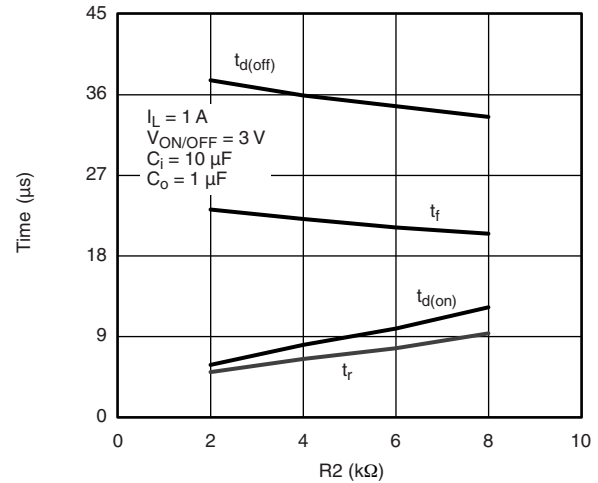
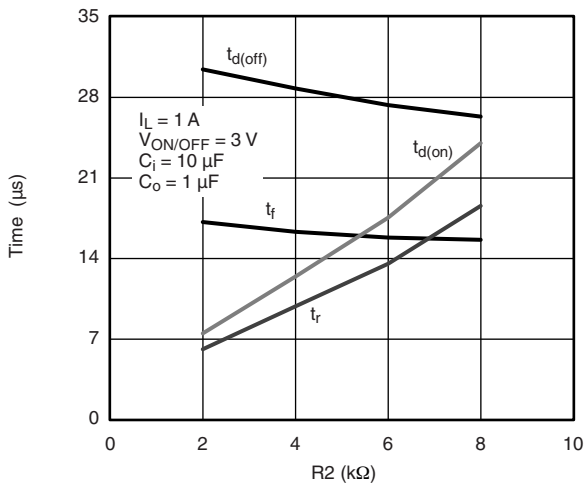
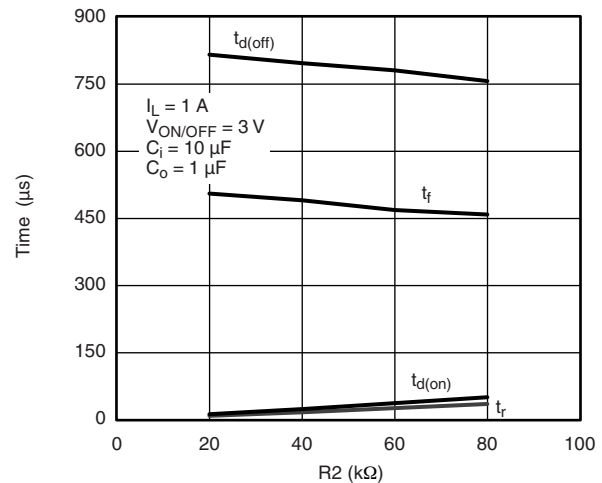
V_{DROP} vs. V_{IN} at $I_L = 1\text{ A}$

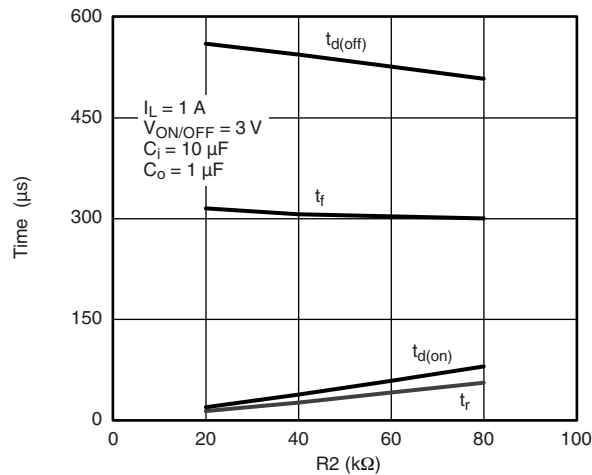


Normalized On-Resistance vs. Junction Temperature

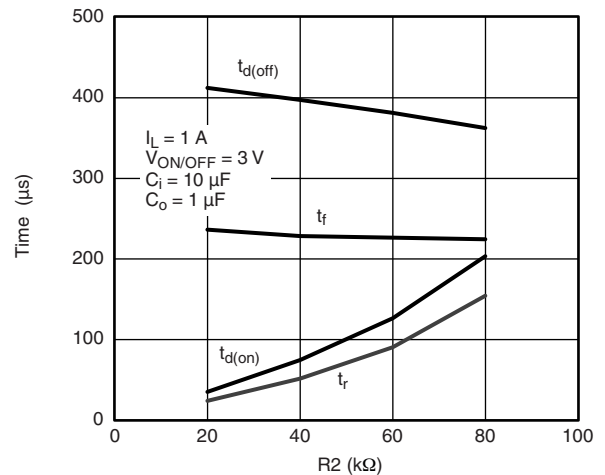
Si3865CDV

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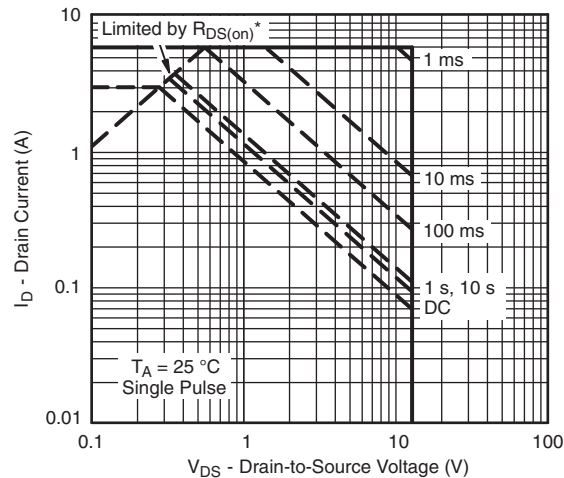
**TYPICAL CHARACTERISTICS** (25 °C, unless otherwise noted)**On-Resistance vs. Input Voltage****Source-Drain Diode Forward Voltage****Switching Variation**
 R_L at $V_{IN} = 4.5\text{ V}$, $R_1 = 20\text{ k}\Omega$ **Switching Variation**
 R_L at $V_{IN} = 2.5\text{ V}$, $R_1 = 20\text{ k}\Omega$ **Switching Variation**
 R_L at $V_{IN} = 1.8\text{ V}$, $R_1 = 20\text{ k}\Omega$ **Switching Variation**
 R_L at $V_{IN} = 4.5\text{ V}$, $R_1 = 300\text{ k}\Omega$

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)


Switching Variation
 R2 at $V_{\text{IN}} = 2.5 \text{ V}$, $R_1 = 300 \text{ k}\Omega$

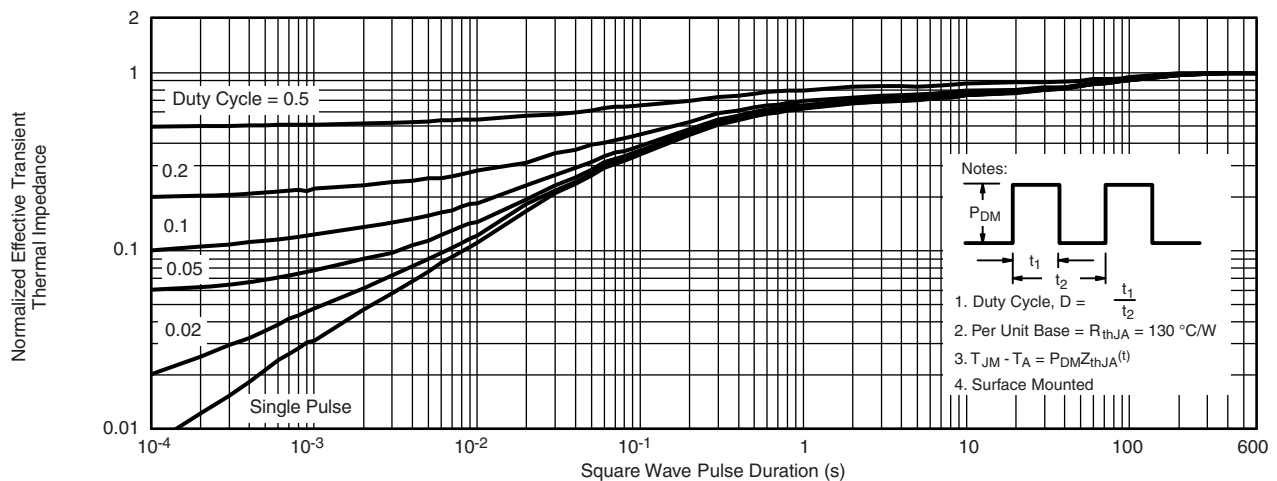


Switching Variation
 R2 at $V_{\text{IN}} = 1.8 \text{ V}$, $R_1 = 300 \text{ k}\Omega$



* $V_{\text{GS}} >$ minimum V_{GS} at which $R_{\text{DS(on)}}$ is specified

Safe Operating Area, Junction-to-Foot



Normalized Thermal Transient Impedance, Junction-to-Ambient

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